Vishay Siliconix

HALOGEN

FREE

Symmetric Dual N-Channel 60 V (D-S) MOSFET

PowerPAIR® 6 x 5FS

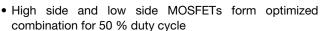
Top View

Bottom View

PRODUCT SUMMARY				
V _{DS} (V)	60			
$R_{DS(on)}$ max. (Ω) at $V_{GS} = 10 \text{ V}$	0.0026			
$R_{DS(on)}$ max. (Ω) at $V_{GS} = 4.5 \text{ V}$	0.0042			
Q _g typ. (nC)	25.6			
I _D (A) ^a	110			
Configuration	Dual			

FEATURES

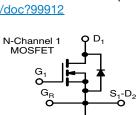
- TrenchFET® Gen IV power MOSFET
- 100 % R_a and UIS tested
- Symmetric dual N-channel
- · Flip chip technology optimal thermal design



· Material categorization: for definitions of compliance please see www.vishav.com/doc?99912

APPLICATIONS

- Buck-boost
- · Half-bridge synchronous rectification
- Telecom DC/DC
- · Motor drive control



G ₁ G _R	S ₁ -D ₂
G ₂	<u></u>
N-Channel 2 MOSFET	S ₂

ORDERING INFORMATION	
Package	PowerPAIR 6 x 5FS
Lead (Pb)-free and halogen-free	SiZF660LDT-T1-GE3

PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-source voltage		V _{DS} 60			
Gate-source voltage		V _{GS}	± 20	V	
Continuous drain current (T _J = 150 °C)	T _C = 25 °C		110		
	T _C = 70 °C		88		
	T _A = 25 °C	I _D	28 b, c		
	T _A = 70 °C		23 b, c		
Pulsed drain current (t = 100 μs)		I _{DM}	400	A	
	T _C = 25 °C		42		
Continuous source-drain diode current	T _A = 25 °C	I _S	3.8 b, c		
Single pulse avalanche current	. 0.411	I _{AS}	40		
Single pulse avalanche energy	L = 0.1 mH	E _{AS}	88	mJ	
	T _C = 25 °C		62.5		
Maximum power dissipation	T _C = 70 °C	Б.	40	14/	
	T _A = 25 °C	P _D	4.2 ^{b, c}	W	
	T _A = 70 °C		2.7 b, c		
Operating junction and storage temperatu	ire range	T _J , T _{stg}	-55 to +150	90	
Soldering recommendations (peak temperature) d, e		, and the second	260	°C	

Notes

- a. $T_C = 25 \,^{\circ}C$
- b. Surface mounted on 1" x 1" FR4 board

e. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components

See solder profile (www.vishav.com/doc?73257). The PowerPAIR is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection

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THERMAL RESISTANCE RATINGS						
PARAMETER		SYMBOL	TYP.	MAX.	UNIT	
Maximum junction-to-ambient a, b	t ≤ 10 s	R_{thJA}	24	30	°C/W	
Maximum junction-to-case (source)	Steady state	R_{thJC}	1.6	2.0		

Notes

- a. Surface mounted on 1" x 1" FR4 board
- b. Maximum under steady state conditions is 60 °C/W for channel-1 and channel-2

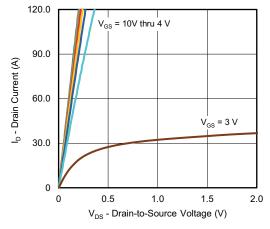
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT	
Static							
Drain-source breakdown voltage	V_{DS}	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	60	-	-	V	
V _{DS} temperature coefficient	$\Delta V_{DS}/T_{J}$	I _D = 10 mA	-	32	-	\//90	
V _{GS(th)} temperature coefficient	$\Delta V_{GS(th)}/T_{J}$	I _D = 250 μA	-	-5.5	-	mV/°C	
Gate-source threshold voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = 250 \mu A$	1	-	2.4	V	
Gate-source leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20$	-	-	± 100	nA	
Zero gate voltage drain current		V _{DS} = 60 V, V _{GS} = 0 V	-	-	1	μA - Ω	
	I _{DSS}	$V_{DS} = 60 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 70 ^{\circ}\text{C}$	-	-	10		
During a second of the second	5	$V_{GS} = 10 \text{ V}, I_D = 10 \text{ A}$	-	0.0020	0.0026		
Drain-source on-state resistance a	R _{DS(on)}	$V_{GS} = 4.5 \text{ V}, I_D = 10 \text{ A}$	-	0.0030	0.0042		
Forward transconductance a	9 _{fs}	$V_{DS} = 15 \text{ V}, I_D = 40 \text{ A}$	-	142	-	S	
Dynamic ^b							
Input capacitance	C _{iss}		-	4315	-	pF	
Output capacitance	C _{oss}	$V_{DS} = 30 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$	i	755	-		
Reverse transfer capacitance	C _{rss}		-	35	-		
Tabella de de com	0	$V_{DS} = 30 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 15 \text{ A}$	-	57	85	nC	
Total gate charge	Qg		-	25.6	39		
Gate-source charge	Q _{gs}	$V_{DS} = 30 \text{ V}, V_{GS} = 4.5 \text{ V}, I_D = 15 \text{ A}$	-	12	-		
Gate-drain charge	Q _{gd}		-	6.1	-		
Output charge	Q _{oss}	$V_{DS} = 30 \text{ V}, V_{GS} = 0 \text{ V}$	-	51	-		
Gate resistance	R_{g}	f = 1 MHz	0.26	1.3	2.6	Ω	
Turn-on delay time	t _{d(on)}		-	15	30		
Rise time	t _r	$V_{DD} = 30 \text{ V}, R_1 = 3 \Omega, I_D \cong 10 \text{ A},$	-	6	15		
Turn-off delay time	t _{d(off)}	$V_{GEN} = 10 \text{ V}, R_g = 1 \Omega$	-	43	90		
Fall time	t _f		ı	8	20		
Turn-on delay time	t _{d(on)}		-	32	65	ns	
Rise time	t _r	$V_{DD} = 30 \text{ V}, R_1 = 3 \Omega, I_D \cong 10 \text{ A},$	-	83	170		
Turn-off delay time	t _{d(off)}	$V_{GEN} = 4.5 \text{ V}, R_g = 1 \Omega$	-	43	90		
Fall time	t _f		-	13	30		
Drain-Source Body Diode Characterist	ics				L		
Continuous source-drain diode current	Is	T _C = 25 °C	-	-	57		
Pulse diode forward current	I _{SM}	-		-	400	A	
Body diode voltage	V_{SD}	I _S = 10 A, V _{GS} = 0 V	-	0.76	1.1	٧	
Body diode reverse recovery time	t _{rr}		-	45	90	ns	
Body diode reverse recovery charge	Q _{rr}	1 40 A 31/31 400 A / T 07 00	-	47	95	nC	
Reverse recovery fall time	t _a	$I_F = 10 \text{ A}, \text{ di/dt} = 100 \text{ A/}\mu\text{s}, T_J = 25 ^{\circ}\text{C}$	-	25	-		
Reverse recovery rise time	t _b		-	20	_	ns	

Notes

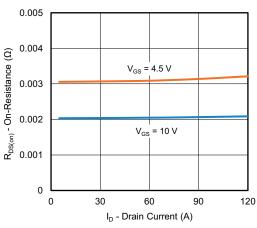
- a. Pulse test; pulse width $\leq 300~\mu s,~duty~cycle \leq 2~\%$
- b. Guaranteed by design, not subject to production testing

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

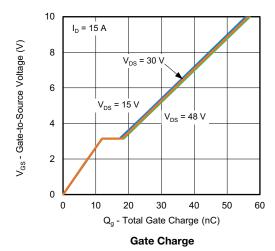


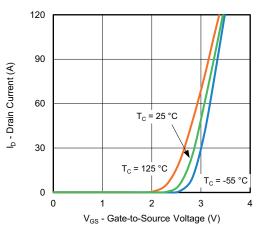


Output Characteristics

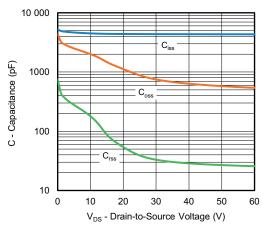


On-Resistance vs. Drain Current

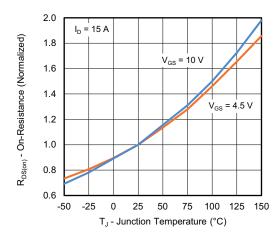




Transfer Characteristics

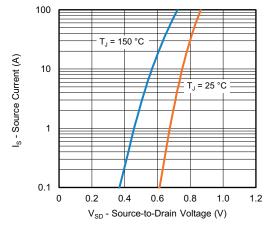


Capacitance

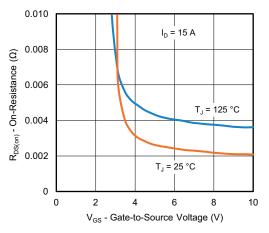


On-Resistance vs. Junction Temperature

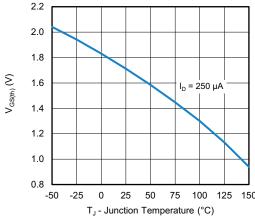




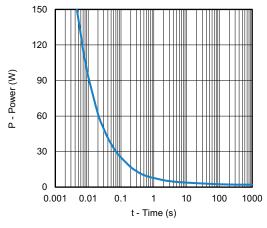
Source-Drain Diode Forward Voltage



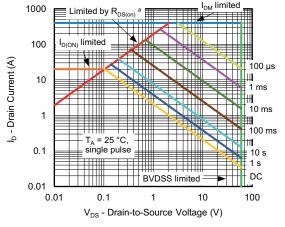
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



Single Pulse Power, Junction-to-Ambient

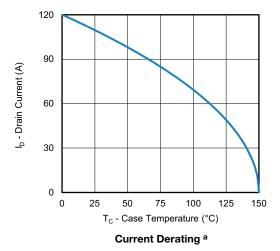


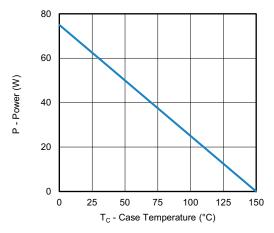
Safe Operating Area, Junction-to-Ambient

Note

a. $V_{GS} > minimum V_{GS}$ at which $R_{DS(on)}$ is specified





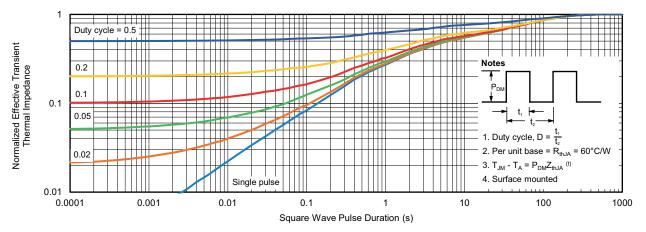


Power, Junction-to-Case

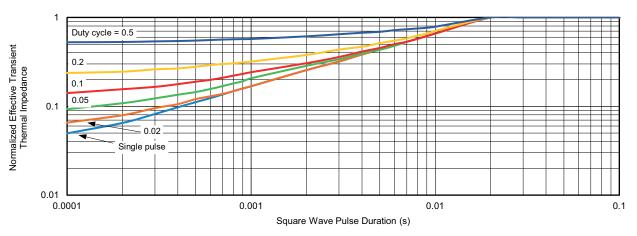
Note

a. The power dissipation P_D is based on T_J max. = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit





Normalized Thermal Transient Impedance, Junction-to-Ambient

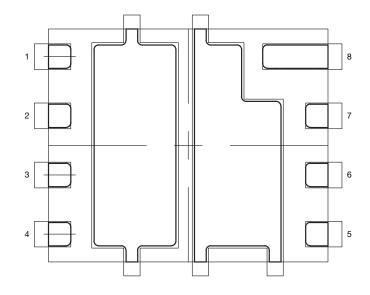


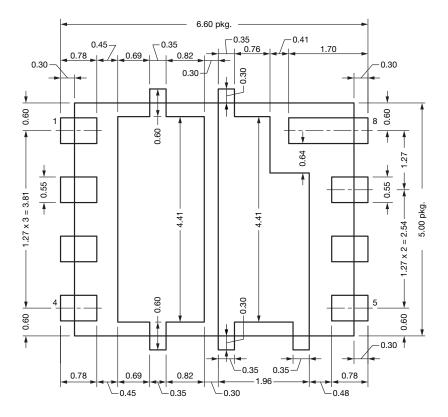
Normalized Thermal Transient Impedance, Junction-to-Case

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package / tape drawings, part marking, and reliability data, see www.vishay.com/ppg?61588.



Recommended Land Pattern PowerPAIR® 6 x 5 FS and PowerPAIR® 6 x 5 FSW





Note

• Dimensions in mm

T24-0311-Rev. A, 09-Sep-2024 DWG: 3030



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